

Amendment to Claims

This listing of Claims will replace all prior versions and listings of claims in this Application.

Listing of Claims

Claims 1 - 4. CANCELLED

Claim 5. (ORIGINAL) A method of chemical vapor deposition (CVD) of copper films comprising:

- preparing a substrate, including forming structures thereon have a barrier metal exposed surface;
- placing the prepared substrate into a CVD chamber;
- heating the substrate to a temperature of between about 200°C and 250°C;
- introducing a water flow in a carrier gas for at least one minute at a water flow of between about 0.005 ml/min and 0.010 ml/min;
- stopping the water flow; and
- starting the flow of copper precursor.

Claim 6. (ORIGINAL) The method of claim 5 wherein said introducing a water flow includes providing a carrier gas taken from the group of carrier gases consisting of Ar, He and N₂.

Claim 7. (ORIGINAL) The method of claim 5 wherein said introducing a water flow includes allowing the water flow to last for a maximum of five minutes.

Claim 8. (ORIGINAL) The method of claim 5 wherein said introducing a water flow includes providing a water vapor flow of between about 100 sccm and 150 sccm.

Claims 9 - 11. CANCELLED

Claim 12. (ORIGINAL) A method of chemical vapor deposition (CVD) of copper films

Page 2 Response to Office Action under 37 C.F.R. § 1.111 for Serial No. 09/978,434

comprising:

preparing a substrate, including forming structures thereon have a barrier metal exposed surface;

placing the prepared substrate into a CVD chamber;

heating the substrate to a temperature of between about 200°C and 250°C;

introducing a water flow of between about 0.005 ml/min and 0.010 ml/min, in a carrier gas for between about at least one minute and five minutes;

stopping the water flow; and

starting the flow of copper precursor.

Claim 13. (ORIGINAL) The method of claim 12 wherein said introducing a water flow wherein the carrier gas is taken from the group of carrier gases consisting of Ar, He and N₂.

Claim 14. (ORIGINAL) The method of claim 12 wherein said introducing a water flow includes providing a water vapor flow of between about 100 sccm and 150 sccm.